

Silicon NPN Power Transistors

2SC4544

DESCRIPTION

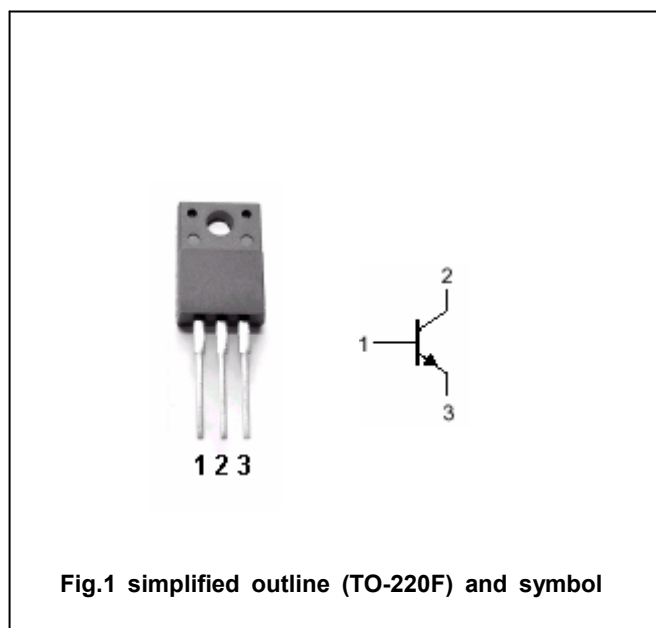
- With TO-220F package
- High Voltage

APPLICATIONS

- Color TV horizontal driver applications
- Color TV chroma output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

**Absolute maximum ratings (Ta=25℃)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		100	mA
I_B	Base current		50	mA
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	2	W
		$T_C=25^\circ\text{C}$	8	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =100μA; I _B =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10μA; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =10mA; I _B =1mA			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =10mA; I _B =1mA			1.0	V
h _{FE-1}	DC current gain	I _C =4mA; V _{CE} =10V	20			
h _{FE-2}	DC current gain	I _C =20mA; V _{CE} =10V	30		200	
I _{CBO}	Collector cut-off current	V _{CB} =240V; I _E =0			1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			1.0	μA
C _{OB}	Output capacitance	I _E =0; V _{CB} =20V; f=1MHz		3		pF
f _T	Transition frequency	I _C =20mA; V _{CE} =10V	50	70		MHz

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PACKAGE OUTLINE

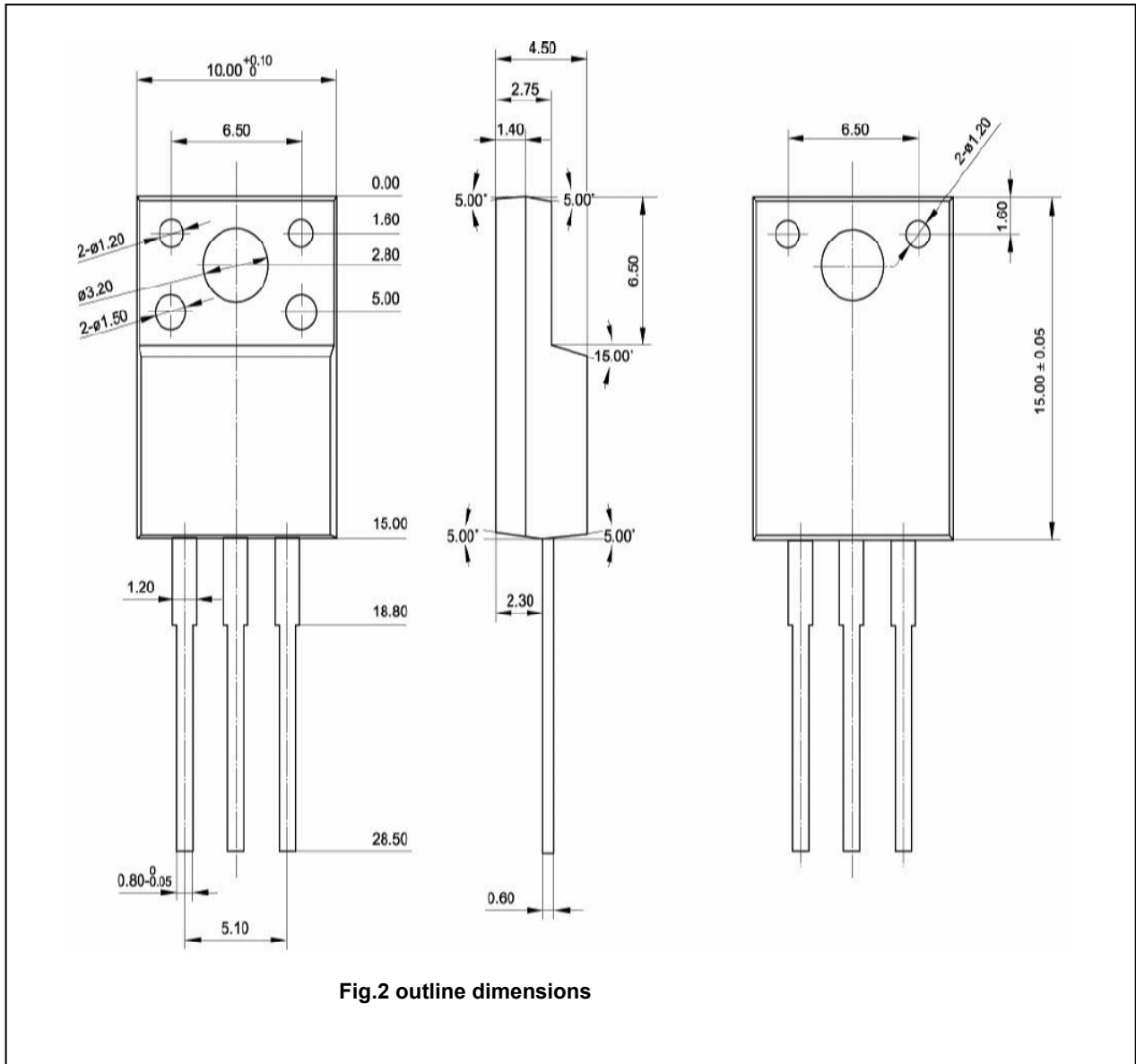


Fig.2 outline dimensions